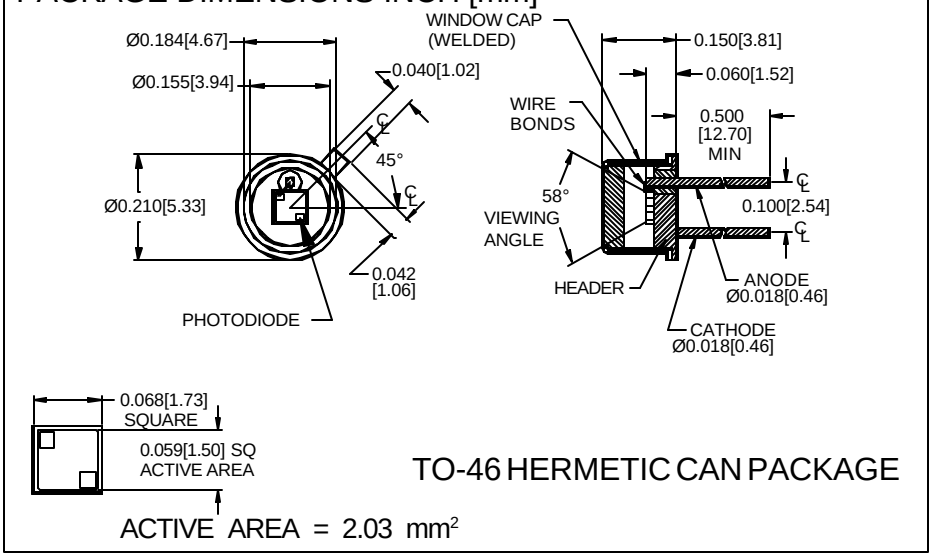
PHOTONIC DETECTORS INC.

Silicon Photodiode, U.V. Enhanced Photoconductive
Type PDU-C103

PACKAGE DIMENSIONS INCH [mm]



TO-46 HERMETIC CAN PACKAGE

ACTIVE AREA = 2.03 mm^2

FEATURES

- High Speed
- U.V. enhanced
- Low capacitance
- U.V. window

DESCRIPTION

The **PDU-C103** is a silicon, PIN planar diffused, U.V. enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic TO-46 metal can with a U.V. transmitting window.

APPLICATIONS

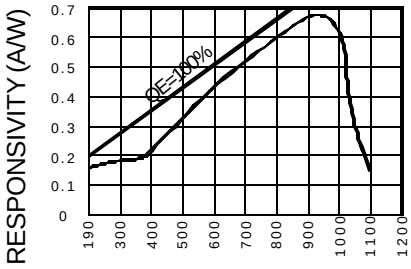
- Spectrometers
- Fluorescent analysers
- U.V. meters
- Colorimeters

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V_{BR}	Reverse Voltage		30	V
T_{STG}	Storage Temperature	-55	+150	°C
T_O	Operating Temperature Range	-40	+125	°C
T_S	Soldering Temperature*		+240	°C
I_L	Light Current		500	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{SC}	Short Circuit Current	H = 100 fc, 2850 K	20	25		μA
I_D	Dark Current	H = 0, V_R = 5 V		65	250	pA
R_{SH}	Shunt Resistance	H = 0, V_R = 10 mV	.25	1		GΩ
TCR_{SH}	RSH Temp. Coefficient	H = 0, V_R = 10 mV		-8		% / °C
C_J	Junction Capacitance	H = 0, V_R = 5 V**		20		pF
λrange	Spectral Application Range	Spot Scan	190		1100	nm
R	Responsivity	V_R = 0 V, λ = 254 nm	.12	.18		A/W
V_{BR}	Breakdown Voltage	I = 10 μA	15	25		V
NEP	Noise Equivalent Power	V_R = 10 mV @ Peak		$10x10^{-14}$		$W/\sqrt{Hz}$
tr	Response Time	RL = 1 KΩ V_R = 5 V		45		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1 MHz

[FORM NO. 100-PDU-C103 REV N/C]